NSN 5962-01-379-5721

Memory Microcircuit - Page 1 of 1



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Maximum Power Dissipation Rating:
300.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Bipolar and programmed and tested to mil-std-883
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Bipolar metal-oxide semiconductor
Input Circuit Pattern:
16 input
Case Outline Source And Designator:
D-8 mil-m-38510
Terminal Surface Treatment:
Solder
Product Name:
Programmed array logic
Voltage Rating And Type Per Characteristic:
4.5 volts applied and 5.5 volts applied
Memory Device Type:
Pal
Hybrid Technology Type:
Monolithic
Terminal Type And Quantity:
20 printed circuit
Specification Data:
81349-mil-m-38510 government specification and 67268-8506501ra government standard
Shelf Life:
N/a
Unit Of Measure:
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Demilitarization:
Yes - demil/mli
Fiig:
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